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Brief

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. . . . . 08/530,661  
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Inventor . . . . . Brent Keeth et al.  
Assignee . . . . . Micron Technology, Inc.  
Group Art Unit . . . . . 2503  
Examiner . . . . . N. Kelly  
Attorney's Docket No. . . . . MI22-356  
Title: Semiconductor Memory Circuitry

BRIEF OF APPELLANT

To: Assistant Commissioner For Patents  
Washington, D.C. 20231

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Appellant appeals from the final rejection, mailed September 23, 1997, of Claims 6-10, 18-19, 22-23 and 25-26. This brief is submitted in triplicate. A check for \$1,260 is attached, including the amount of \$310.00 in payment of the filing fee required under 37 C.F.R. §1.17(f) and also including the amount of \$950 for the three-month extension fee due under 37 C.F.R. §1.17(c).

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1 I. REAL PARTY IN INTEREST.

2 The real party in interest of this application is Micron Technology,  
3 Inc. as evidenced by the full assignment of the pending application to  
4 Micron Technology, Inc. recorded at Reel 7671, Frame 0965 in the  
5 Assignment Branch of the Patent and Trademark Office.

6  
7 II. RELATED APPEALS AND INTERFERENCES.

8 Appellant, Appellant's undersigned legal representative, and the  
9 assignee of the pending application are aware of no appeals or  
10 interferences which will directly affect, be directly affected by, or have  
11 a bearing on the Board's decision in the pending appeal.

12  
13 III. STATUS OF THE CLAIMS.

14 Claims 6-10, 18-19, 22-23 and 25-26 are pending, stand finally  
15 rejected, and are being appealed.

16  
17 IV. STATUS OF AMENDMENTS.

18 No amendment to the application has been submitted subsequent  
19 to final rejection.

20  
21 V. SUMMARY OF THE INVENTION.

22 The claimed inventions are memory die or devices having smaller  
23 size or consumed monolithic die area than did prior art devices. (See,  
24 specification at pg. 34, lns. 20-23.) In one aspect, the claimed invention

1 encompasses a 16M semiconductor memory device comprising a total of  
2 from 16,000,000 to 17,000,000 functional and operably addressable  
3 memory cells occupying an area on a semiconductor die which is no  
4 greater than 14 mm<sup>2</sup>. (See, for example, specification at pg. 37,  
5 lns. 15-21.)

6 In another aspect, the above-mentioned 16M semiconductor memory  
7 device further comprises peripheral circuitry and pitch circuitry formed  
8 on the die relative to the memory arrays. (See, for example, specification  
9 at pg. 37, ln. 24 through pg. 38, ln. 3.) The peripheral circuitry, pitch  
10 circuitry and memory arrays have a total combined continuous surface  
11 area which is less than or equal to 35 mm<sup>2</sup>. (See, for example,  
12 specification at pg. 38, ln. 3.)

13 In another aspect, the above-mentioned peripheral circuitry, pitch  
14 circuitry and memory arrays have a total combined continuous area on  
15 a die which is less than or equal to 32 mm<sup>2</sup>. (See, for example,  
16 specification at pg. 38, lns. 11-14.)

17 In yet another aspect, the invention encompasses a 16M  
18 semiconductor memory device having a total of from 16,000,000 to  
19 17,000,000 functional and operably addressable memory cells arranged in  
20 multiple memory arrays. (See, for example, specification at pg. 37, lns.  
21 15-18.) At least one of the memory arrays contains at least one area  
22 of 100 square microns of continuous die surface area which has at least  
23 128 of the functional and operably addressable memory cells. (See, for  
24 example, specification at pg. 38, lns. 3-6.)

1 In another aspect, the above-mentioned at least one area of 100  
2 square microns has at least 170 of the functional and operably  
3 addressable memory cells. (See, for example, specification at pg. 38,  
4 lns. 14-16.)

5  
6 **VI. ISSUE.**

7 Are the inventions of claims 6-10, 18-19, 22-23 and 25-26  
8 sufficiently described in the specification such that a person of ordinary  
9 skill in the art is enabled to make and use the inventions within the  
10 meaning of 35 U.S.C. § 112 ¶ 1?

11  
12 **VII. GROUPING OF CLAIMS.**

13 Claims 6-10, 18-19, 22-23 and 25-26 stand or fall as one group.

14  
15 **VIII. ARGUMENT.**

16 **A. Summary Of The Examiner's Rejections.**

17 Claims 6-10, 18-29, 22-23 and 25-26 stand rejected under 35 U.S.C.  
18 § 112 ¶ 1. (Paper 12, pg. 2, ¶ 2.) The Examiner indicates that  
19 Applicant's disclosure describes various improvements for producing  
20 Applicant's claimed structures, and contends that one or more of such  
21 improvements are critical or essential to the practice of Applicant's  
22 invention. (Paper 12, pg. 2, ¶ 2.) The Examiner states that since the  
23 improvements are not included in Applicant's claims, the claimed  
24 structures are not enabled by Applicant's disclosure. (Paper 12, pg. 2,

1 ¶ 2.) *In re Mayhew*, (527 F.2d 1229, 188 USPQ 356 (CCPA 1976)) is  
2 cited to support the position that Applicant's claims are not enabled.

3 The Examiner further states that the need to utilize one or more  
4 of Applicant's disclosed improvements to practice Applicant's claimed  
5 methods is evidenced by the novelty and non-obviousness of Applicant's  
6 invention. (Paper 12, pg. 3, ¶ 3.) Specifically, the Examiner contends  
7 that since Applicant's claimed structures were not known in the prior  
8 art, Applicant's disclosed methods of forming the structures must be  
9 essential for producing such claimed structures. (Paper 12, pg. 3, ¶ 3.)  
10

11 B. The Specification And Claims Comply With 35 U.S.C.  
12 § 112 ¶ 1.

13 The Examiner is mistaken in his contention that Applicant's claims  
14 lack enablement. The *Mayhew* ruling is not applicable to the present  
15 case for at least the reason that its facts are not analogous to the  
16 present facts.

17 In *Mayhew*, the court found that an Appellant's specification  
18 indicated that certain components were essential for a claimed method  
19 invention. (See, 188 USPQ at p. 358.) Such essential components  
20 pertained to the utilization and location of a cooling apparatus. The  
21 *Mayhew* specification stated that a strip and bath are "raised in  
22 temperature above what is ordinarily considered optimum coating  
23 temperatures. *This is practical because of special cooling apparatus,*  
24 *specially located.*" (Emphasis by the court) (188 USPQ at p. 358.) Also,

1 the *Mayhew* specification stated "if high temperature galvanizing spelter  
2 were present in zone 54, iron dissolution and dross formation would  
3 make it *impossible to produce the smooth coat produced by the present*  
4 *invention.*" (Emphasis added by the court.) (188 USPQ at p. 361.) The  
5 *Mayhew* Court determined that the statements of the specification  
6 indicated that the cooling apparatus and its location were essential to  
7 Mayhew's invention. (See, 188 USPQ at p. 358.) As evidenced by the  
8 above-quoted sections of Mayhew's specification, it unambiguously stated  
9 that the recited invention required (i.e., was impossible without) specific  
10 embodiments set forth in the specification. Accordingly, the Court held  
11 that method claims failing to recite such essential steps were not  
12 enabled by the specification. (See, 188 USPQ at p. 358.)

13 In contrast to the specification of *Mayhew*, Applicant's specification  
14 contains no language indicating that Applicant's claims are to be  
15 confined solely to disclosed embodiments. To the contrary, Applicant's  
16 disclosure states exactly the opposite, that "[o]ne or more of the  
17 [disclosed] techniques, or other techniques, can be utilized in the  
18 production of 64M, 16M or 4M memory chips in accordance with the  
19 invention, with the invention only being limited by the accompanying  
20 claims appropriately interpreted in accordance with the Doctrine of  
21 Equivalents." (P. 9. Ins. 3-7 of Applicant's specification, emphasis  
22 added.) The disclosure further states that the specifically disclosed  
23 methods of achieving high device density are provided by way of  
24

1 example only and not by way of limitation. (See, for example, p. 37,  
2 lns. 21-24; and p. 39, lns. 5-8.)

3 As the above-discussed statements illustrate, Applicant's disclosure  
4 does not expressly limit the invention to the disclosed embodiments, but  
5 rather specifically indicates that such limitation is not to occur. Thus,  
6 unlike the disclosure at issue in *Mayhew*, Applicant's disclosure cannot  
7 reasonably be interpreted to require that any of Applicant's disclosed  
8 embodiments are essential to Applicant's claimed inventive structure.  
9 For at least this reason, the Examiner's rejections of claims 6-10, 18-19,  
10 22-23 and 25-26 are improper and should be reversed.

11 The facts of the present case are analogous to those presented in  
12 *Beale v. Schuman*, 212 USPQ 291 (BOPI 1980). In *Beale*, the Board  
13 explained that *Mayhew* is inapplicable to cases in which an Applicant's  
14 disclosure provides nothing requiring claims to be confined solely to  
15 disclosed embodiments. (212 USPQ at 293.) The disclosure in *Beale*  
16 concerned a free-piston engine with means provided to permit a working  
17 gas to leak by the piston. The *Beale* specification only disclosed  
18 embodiments in which gas passages were provided on cylinder walls.  
19 (See, 212 USPQ at pgs. 291, 293.) Yet, a claim in *Beale* was broad  
20 enough to encompass structures with gas passages formed on either a  
21 cylinder, or on both a piston and a cylinder. (See, 212 USPQ at p.  
22 293.) The Board held that the specification was sufficient to enable the  
23 scope of the claim, and stated  
24



1 We find nothing in the ... disclosure which requires the gas  
2 passages to be confined solely to the cylinder walls. . . An  
3 inventor is not required to limit his claims to a specific  
4 example or examples disclosed in his application.

5 (212 USPQ at p. 293.) From the Board's discussion in *Beale*, it  
6 is apparent that *Mayhew* should be invoked to narrow claims only when  
7 a disclosure indicates that particular steps are required for a claimed  
8 invention. A mere description of specific enabling embodiments or  
9 examples is not enough to indicate that particular steps are required for  
10 an invention. Rather, express language indicating such requirement must  
11 be in a disclosure before *Mayhew* is applicable. Such express language  
12 was provided in *Mayhew*'s disclosure with the statement that certain  
13 results were, a) only "practical" due to specific embodiments set forth  
14 by *Mayhew*; and b) essentially "impossible" without the embodiment which  
15 produced acceptable inventive results.

16 Applicant's disclosure, like the disclosure at issue in *Beale*, contains  
17 no language indicating that Applicant's claims are to be confined solely  
18 to disclosed embodiments. It does just the opposite. Thus, for the  
19 reasons discussed in *Beale*, Applicant's claims should not be limited to  
20 Applicant's disclosed embodiments. The Examiner's rejections of claims  
21 6-10, 18-19, 22-23 and 25-26 are therefore improper and should be  
22 reversed.

23 Further, the claims in *Mayhew* were method, wherein the claims  
24 in *Beale* were article. Applicant's appealed claims are also article.  
Accordingly, the instant facts are analogous to *Beale*, not *Mayhew*, and

1 the *Beale* ruling should be applied here. With respect to *article* claims,  
2 the Board in *Beale* held,

3 "broad claims may be supported by a specific embodiment  
4 ... and an inventor need not limit his claims to precisely  
5 what he has found will work..." (*Beale* at p. 294.)

6 Likewise, Applicant has submitted *article* claims and should not be  
7 compelled to limit such claims to certain disclosed *methods* by which such  
8 are producible. To require such would be to essentially compel product-  
9 by-process claims, which is not what Applicant "regards" as its invention  
10 in the presentation of the appealed claims. Applicant should not be  
11 limited to such claims, even under *Mayhew*, as there is no indicated  
12 requirement or necessity of any method limitations presented by the  
13 specification. Regardless, *Beale* is controlling with respect to Applicant's  
14 *article* claims, not *Mayhew*. Applicant's claims are inherently in  
15 compliance with 35 U.S.C. §112, and under the authority of *Beale*.

16 A final thrust of the Examiner's rejection is an attempt to utilize  
17 the novelty and non-obviousness of Applicant's claimed structure as  
18 evidence that Applicant's disclosed embodiments are essential to the  
19 claimed invention. Such is clearly an improper basis for rejection.  
20 Applicant is aware of no authority indicating that the novelty and non-  
21 obviousness of an invention has any bearing on whether an invention is  
22 enabled, and contends that there is none. If the Examiner's basis of  
23 rejection were accurate, then every claim to novel and non-obvious  
24 structures would need to be limited to only the embodiments specifically  
disclosed in the specification accompanying the claim. Clearly, the

1 Examiner's basis of rejection cannot be accurate. For instance, every  
2 issued patent claim is presumed to be novel and non-obvious, (35  
3 U.S.C. §282), yet every issued claim is not limited to only the  
4 embodiments specifically disclosed in the specification accompanying the  
5 claim. (See, e.g., *Beale*.) Accordingly, the novelty and non-obviousness  
6 of an invention is irrelevant to whether the invention is enabled. For  
7 this additional reason the Examiner's rejections of claims 6-10, 18-19, 22-  
8 23 and 25-26 under 35 U.S.C. § 112 ¶ 1 are improper and should be  
9 reversed.

10  
11 C. Conclusion.

12 For the above-discussed reasons, the Examiner's rejections of  
13 claims 6-10, 18-19, 22-23 and 25-26 are improper. Applicant therefore  
14 requests reversal of the final rejections of claims 6-10, 18-19, 22-23  
15 and 25-26. Allowance of such claims is also respectfully requested.

16 Respectfully submitted,

17  
18 Dated: 3/23/98

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1 IX. APPENDIX A -- THE CLAIMS INVOLVED IN THIS APPEAL.

2  
3 6. A 16M semiconductor memory device comprising:

4 a semiconductor die encapsulated in a package, the package having  
5 an encapsulating body and electrically conductive interconnect pins  
6 extending outwardly from the body;

7 a total of from 16,000,000 to 17,000,000 functional and operably  
8 addressable memory cells arranged in multiple memory arrays formed on  
9 the die, the individual functional and operably addressable memory cells  
10 occupying area on the die within the memory arrays, the occupied area  
11 of all functional and addressable memory cells on the die having a total  
12 combined area which is no greater than 14 mm<sup>2</sup>; and

13 peripheral circuitry and pitch circuitry formed on the die relative  
14 to the memory arrays; the peripheral circuitry electrically interconnecting  
15 with the pins and including operably interconnected control and timing  
16 circuitry, address and redundancy circuitry, data and test path circuitry,  
17 and voltage supply circuitry which collectively enable full access to all  
18 addressable memory cells of the memory arrays.

19  
20 7. The semiconductor memory device of claim 6 wherein the  
21 peripheral circuitry, the pitch circuitry, and the memory arrays are  
22 fabricated to include a total of four or less conductive line layers.

1           8.     The semiconductor memory device of claim 6 wherein the  
2 peripheral circuitry, the pitch circuitry and the memory arrays have a  
3 total combined continuous surface area on the die which is less than or  
4 equal to 35 mm<sup>2</sup>.

5  
6           9.     The semiconductor memory device of claim 6 wherein the  
7 peripheral circuitry, the pitch circuitry, and the memory arrays are  
8 fabricated to include at least five conductive line layers, the occupied  
9 area of all functional and operable memory cells on the die having a  
10 total combined area on the die which is no greater than 11 mm<sup>2</sup>.

11  
12           10.    The semiconductor memory device of claim 6 wherein the  
13 peripheral circuitry, the pitch circuitry, and the memory arrays are  
14 fabricated to include at least five conductive line layers; the peripheral  
15 circuitry, the pitch circuitry and the memory arrays having a total  
16 combined continuous surface area on the die which is less than or equal  
17 to 32 mm<sup>2</sup>.

1           18.    A 16M semiconductor memory device comprising:  
2                a semiconductor die encapsulated in a package, the package having  
3                an encapsulating body and electrically conductive interconnect pins  
4                extending outwardly from the body;  
5                a total of from 16,000,000 to 17,000,000 functional and operably  
6                addressable memory cells arranged in multiple memory arrays formed on  
7                the die, at least one of the memory arrays containing at least one area  
8                of 100 square microns of continuous die surface area having at least 128  
9                of the functional and operably addressable memory cells; and  
10              peripheral circuitry and pitch circuitry formed on the die relative  
11              to the memory arrays; the peripheral circuitry electrically interconnecting  
12              with the pins and including operably interconnected control and timing  
13              circuitry, address and redundancy circuitry, data and test path circuitry,  
14              and voltage supply circuitry which collectively enable full access to all  
15              addressable memory cells of the memory arrays.

16  
17           19.    The semiconductor memory device of claim 18 wherein at  
18           least one of the memory arrays containing at least one area of 100  
19           square microns of continuous die surface area has at least 170 of the  
20           functional and operably addressable memory cells.

1           22. A semiconductor memory device comprising:  
2           a total of no more than 68,000,000 functional and operably  
3 addressable memory cells arranged in multiple memory arrays formed on  
4 a semiconductor die; and  
5           circuitry formed on the semiconductor die permitting data to be  
6 written to and read from one or more of the memory cells, at least  
7 one of the memory arrays containing at least one area of 100 square  
8 microns of continuous die surface area having at least 128 of the  
9 functional and operably addressable memory cells.

10  
11           23. The semiconductor memory device of claim 22 wherein the  
12 total number of functional and operably addressable memory cells on the  
13 semiconductor die is no more than 17,000,000.

14  
15           25. The semiconductor memory device of claim 22 wherein at  
16 least one of the memory arrays containing at least one area of 100  
17 square microns of continuous die surface area has at least 170 of the  
18 functional and operably addressable memory cells.

1           26. The semiconductor memory device of claim 22 wherein at  
2 least one of the memory arrays containing at least one area of 100  
3 square microns of continuous die surface area has at least 170 of the  
4 functional and operably addressable memory cells, and the total number  
5 of functional and operably addressable memory cells on the  
6 semiconductor die is no more than 17,000,000.